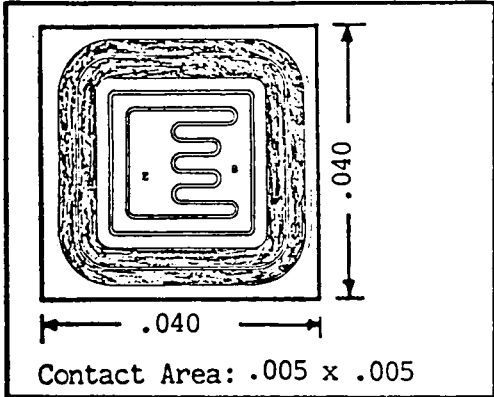


X00220

STX625 CHIP
HIGH VOLTAGE PNP TRANSISTOR CHIP



CONTACT METALLIZATION
 Base/Emitter: > 30,000 Å Aluminum
 Collector: > 2,000 Å Evaporated Gold

ASSEMBLY RECOMMENDATIONS

1. Eutectic Die Attach.
2. Ultrasonically Attach 2 MIL Aluminum Wire To Base/Emitter Contacts.

PARAMETER	TEST CONDITIONS	TYPE	MIN.	MAX.	UNIT
V_{CE0}	$I_C = 1 \text{ mA}$ (pulsed)		450		Vdc
V_{CB0}	$I_C = 100 \text{ uA}$		500		Vdc
V_{CER}	$I_C = 100 \text{ uA}$, $R_{BE} = 5 \text{ K Ohm}$		500		Vdc
V_{EBO}	$I_E = 20 \text{ uA}$				Vdc
I_{EBO}	$V_{EB} = 4 \text{ V}$			250	mA
I_{CB0}	$V_{CB} = 500 \text{ V}$			500	mA
h_{FE}	$V_{CE} = 10 \text{ V}$, $I_C = 1 \text{ mA}$		20	200	
h_{FE}	$V_{CE} = 10 \text{ V}$, $I_C = 25 \text{ mA}$		40	250	
h_{FE}	$V_{CE} = 15 \text{ V}$, $I_C = 100 \text{ mA}$		20	200	
$V_{BE(SAT)}$	$I_C = 25 \text{ mA}$, $I_B = 2.5 \text{ mA}$			1.0	Vdc
$V_{CE(SAT)}$	$I_C = 25 \text{ mA}$, $I_B = 2.5 \text{ mA}$			3.0	Vdc
C_{OB}	$V_{CB} = 15 \text{ V}$			20	pf
f_T	$V_{CE} = 20 \text{ V}$, $I_C = 10 \text{ mA}$ $f = 5 \text{ MHz}$		20		MHz

Electrical characteristics measured at lot acceptance testing in a TO-5 package. Specifications subject to change without notice.

SSDI SOLID STATE DEVICES, INC.

P.O. Box 577, La Mirada, California, 90637-0577 TWX 910-583-4807
 14830 Valley View Avenue, La Mirada, California, 90638 (213) 921-9660